

Thin film Layers



- Totally customized
- Dry oxidation
- Breakdown voltage:
>200 V for 285 nm thick
layer
- Low Roughness
($< 3 \text{ \AA RMS}$)
- Any metallic layers
- Multilayers deposition

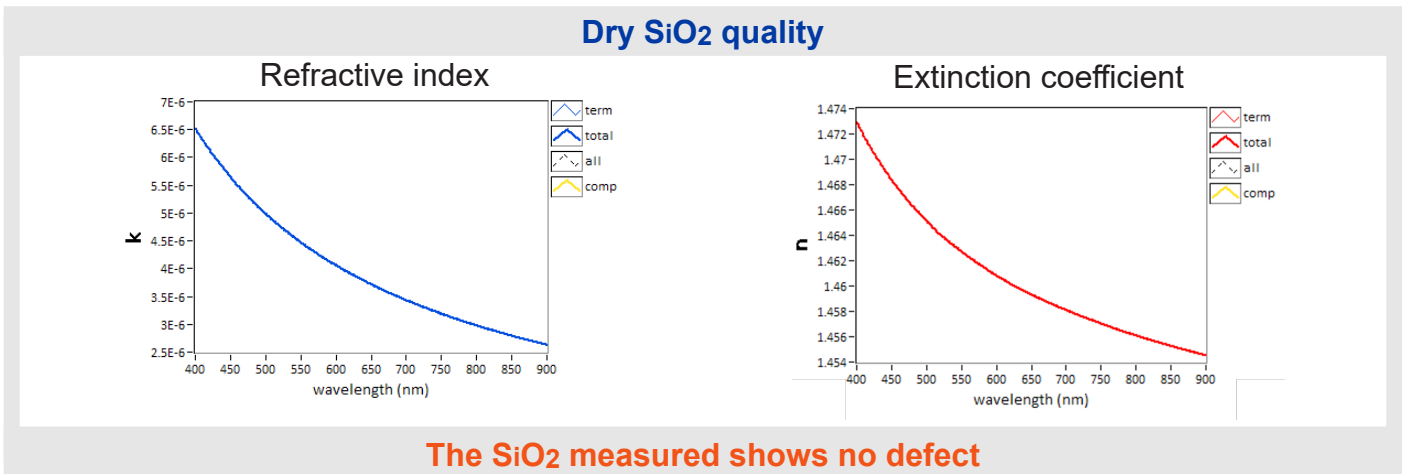


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silicon technologies

Oxidation & Deposition on Silicon	Thickness (nm)	Thickness tolerances (µm)	Diameters
Oxidation			
Wet oxidation	200 - 3000	± 3%	From 1" to 6"
High purity dry oxidation	20 - 300	± 5%	From 1" to 6"
Option			
Single face oxidation			



Single layer deposition / metallization				
Silicon nitride	LPCVD	20 - 500	Option: Low Stress	From 2" to 6"
	PECVD			
Oxide nitride	PECVD	20 - 500	From 1" to 6"	From 2" to 4"
Polysilicon	LPCVD	20 - 600	From 1" to 4"	
Cr, Ti, Au, Al, Pt, Mo, W Highly reflective silver coating	PVD sputtering			
Ni, Cu, Ir, Ta, Al ₂ O ₃	Evaporation	20 - 1000	± 10%	From 1" to 6" depending on metals
Cr/Au TiW with Ti : 10% W: 90% TiW /Au with Ti : 10% W: 90% Ti/Pt	PVD			

Multilayers deposition
On request

